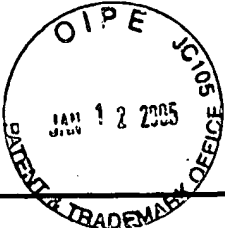


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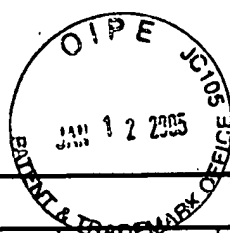
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| | SERIAL NO.: 10/802,185 |
| | FILING DATE: March 17, 2004 |
| | GROUP: 2813 |

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